

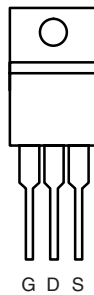
N-Channel 150-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
150	0.095 at $V_{GS} = 10$ V	18
	0.100 at $V_{GS} = 6$ V	17.5

FEATURES

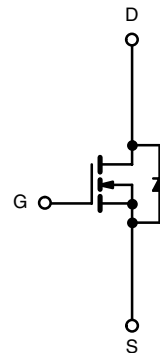
- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature


RoHS*
COMPLIANT

TO-220AB


Top View

DRAIN connected to TAB



N-Channel MOSFET

Ordering Information: SUP18N15-95
SUP18N15-95-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	150	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	18	A
		$T_C = 125$ °C	10.3	
Pulsed Drain Current	I_{DM}	25		
Avalanche Current	I_{AS}	15		
Single Pulse Avalanche Energy ^a	E_{AS}	16.2	mJ	
Maximum Power Dissipation ^a	P_D	88 ^b	W	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (Free Air)	R_{thJA}	85	°C/W	
Junction-to-Case	R_{thJC}	1.7		

Notes:

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.

* Pb containing terminations are not RoHS compliant, exemptions may apply.



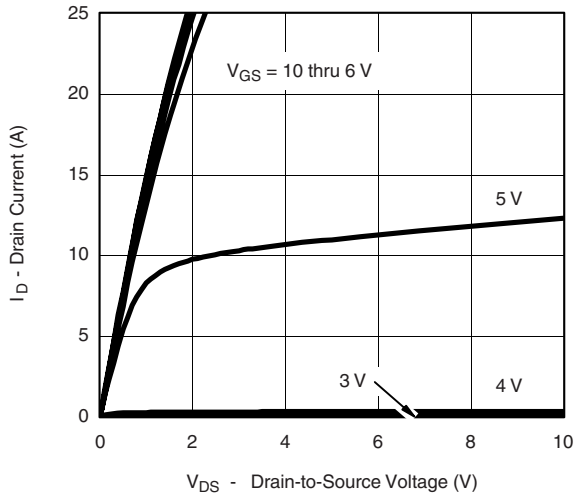
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2			
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	25			A
Drain-Source On-State Resistance ^b	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		0.077	0.095	Ω
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.190	
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.250	
		$V_{GS} = 6\text{ V}, I_D = 10\text{ A}$		0.081	0.100	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		25		S
Dynamic^a						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		900		pF
Output Capacitance	C_{oss}			115		
Reverse Transfer Capacitance	C_{rss}			70		
Total Gate Charge ^c	Q_g	$V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		20	25	nC
Gate-Source Charge ^c	Q_{gs}			5.5		
Gate-Drain Charge ^c	Q_{gd}			7		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 75\text{ V}, R_L = 5\text{ }\Omega$ $I_D \cong 15\text{ A}, V_{GEN} = 10\text{ V}, R_G = 2.5\text{ }\Omega$		8	12	ns
Rise Time ^c	t_r			35	55	
Turn-Off Delay Time ^c	$t_{d(off)}$			17	25	
Fall Time ^c	t_f			30	45	
Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$) ^b						
Continuous Current	I_S				15	A
Pulsed Current	I_{SM}				25	
Forward Voltage ^a	V_{SD}	$I_F = 15\text{ A}, V_{GS} = 0\text{ V}$		0.9	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 15\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		55	85	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			5	8	A
Reverse Recovery Charge	Q_{rr}			0.13	0.34	μC

Notes:

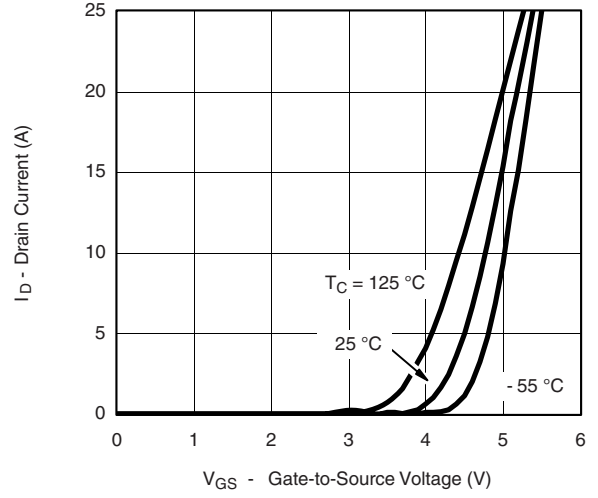
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

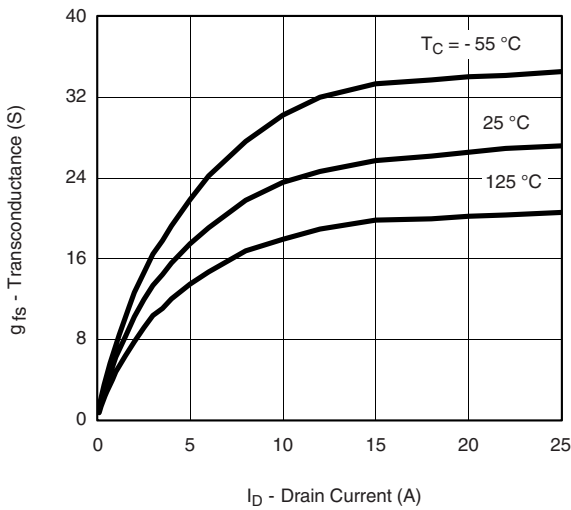
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



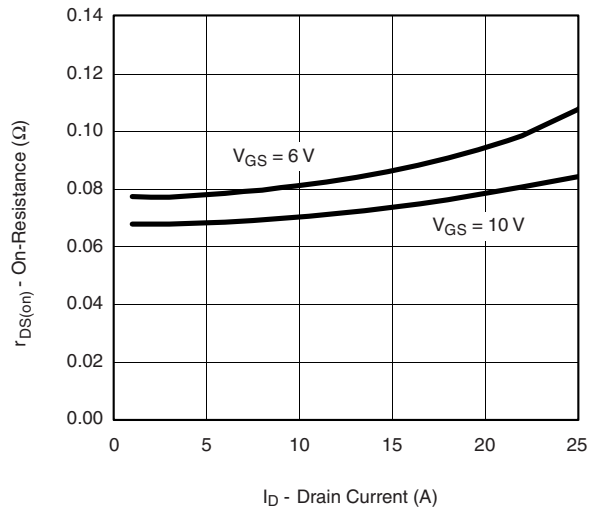
Output Characteristics



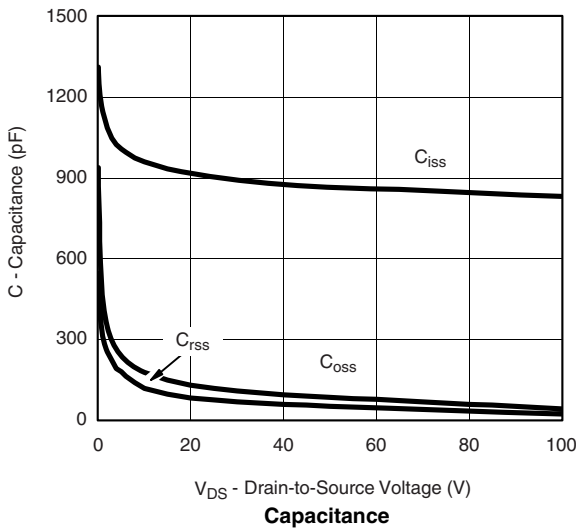
Transfer Characteristics



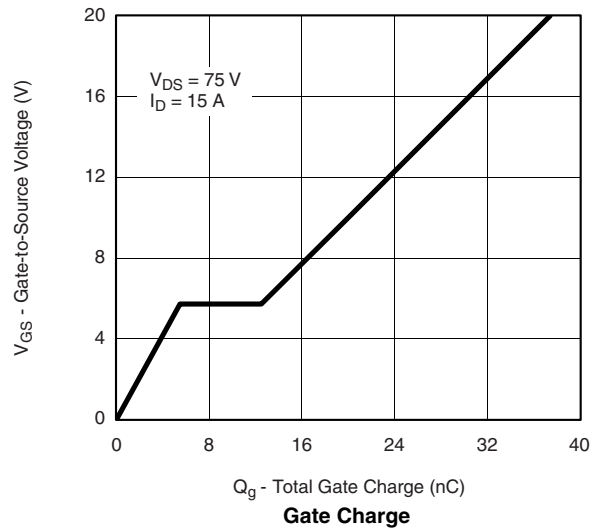
Transconductance



On-Resistance vs. Drain Current

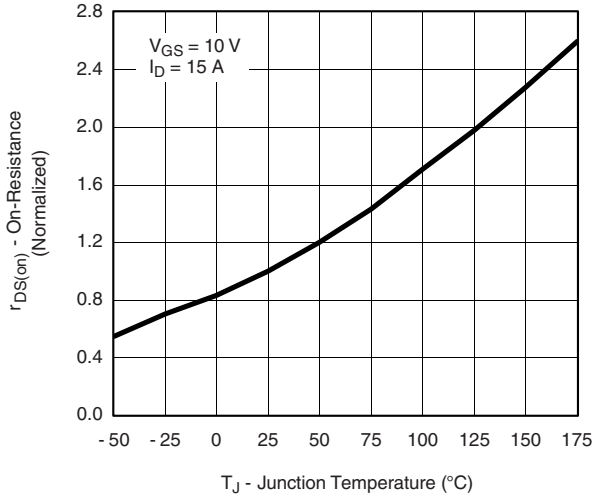


Capacitance

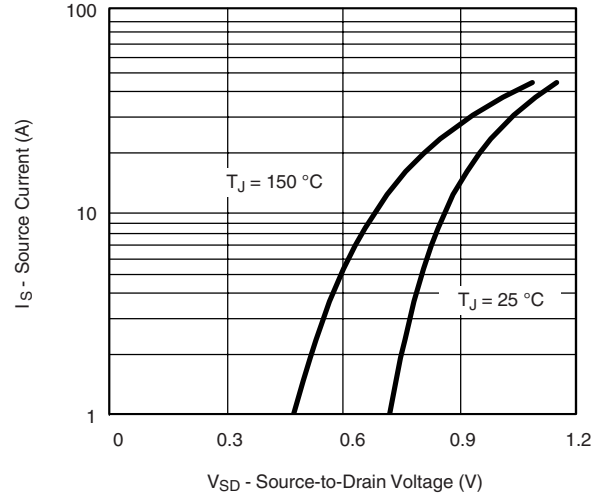


Gate Charge

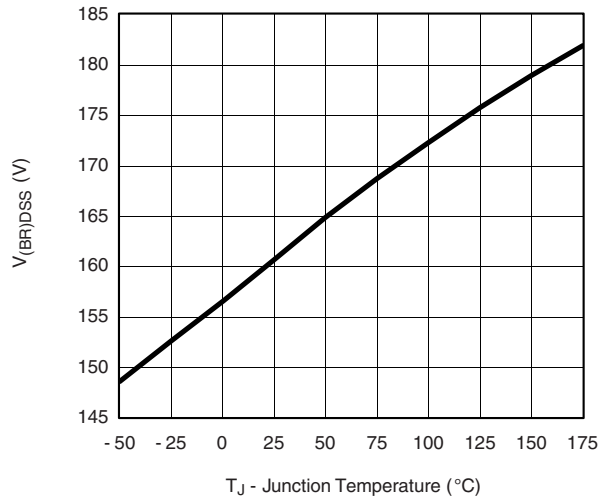
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Junction Temperature

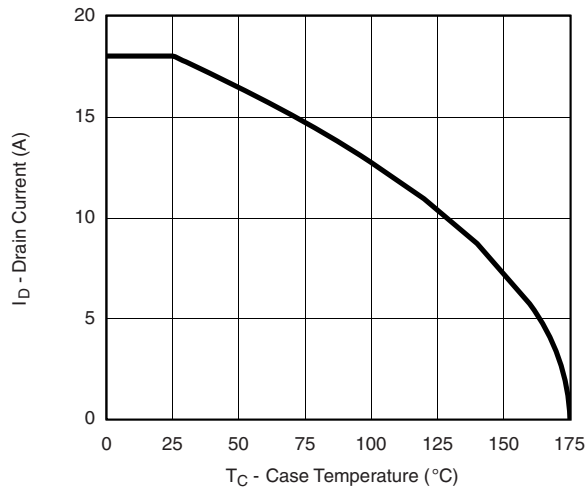


Source-Drain Diode Forward Voltage

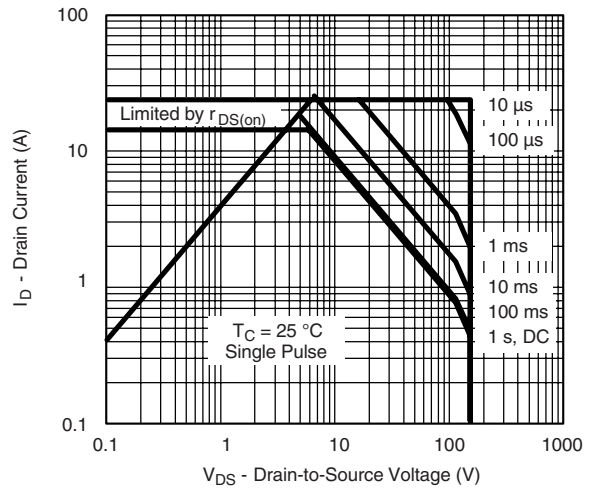


Drain-Source Voltage Breakdown vs. Junction Temperature

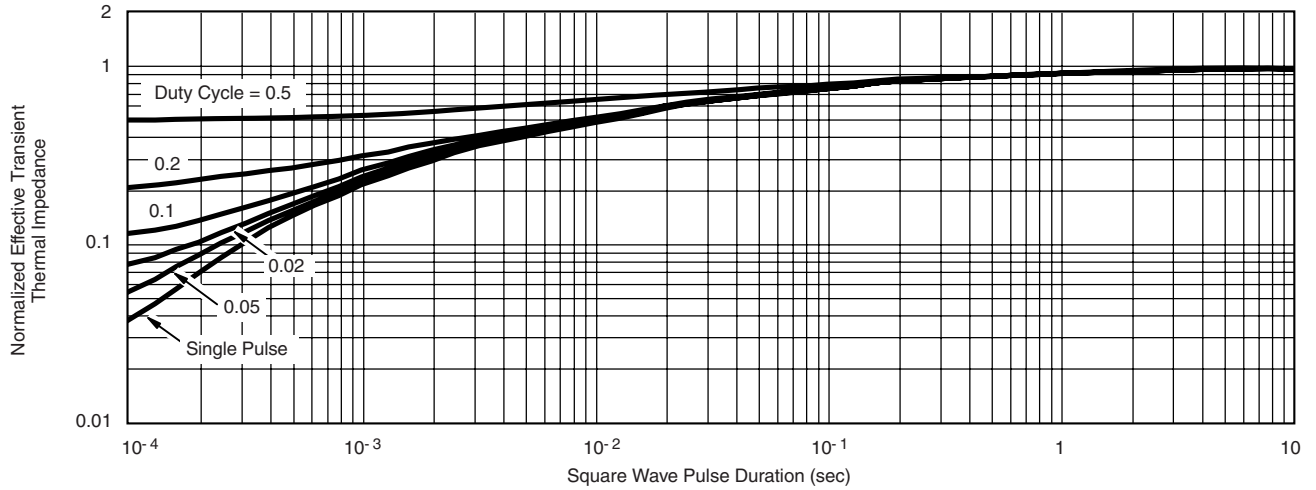
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?71642>.



Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Vishay\(威世\)](#)